

MIG20065A

650V Silicon Carbide Schottky Diode

DESCRIPTION :

- High Surge Currenr
- No reverse recovery
- Positive temperature Coefficient
- · Easy to paralleling
- RoHS Compliant

TYPICAL APPLICATIONS:

- Power factor correction
- Data Center
- Switch mode power supplies
- Solar inverter

V _{RRM}	650V
I _F	20A (TC=154°C)
Q _C	62nC



TO-220AC

MAXIMUM RATINGS (at $T_C = 25$ °C, unless otherwise specified)

Characteristic	Condition	Symbol	Value	Unit
Repetitive Peak Reverse Voltage		V _{RRM}	650	V
Continuous Forward Current	Tc=25℃ Tc=135℃ Tc=154℃	I _F	62 29 20	А
Non-Repetitive Forward Surge Current	Tc=25°C , t_P=10ms, Half sine pulse Tc=110°C , t_P=10ms, Half sine pulse	I _{FSM}	172 156	А
Repetitive Peak Forward Surge Current	Tc=25 $^\circ\!\!\mathbb{C}$, tp=10ms, Half sine pulse	I _{FRM}	164	А
i ² t value	Tc=25℃ , tբ=10ms Tc=110℃ , tբ=10ms	∫ i²dt	148 121	A ² S
Power dissipation	Tc=25℃ Tc=110℃ Tc=150℃	P _{tot}	258 112 43	w
Operation Junction temperature		Tj	-55~+175	°C
Storage temperature		T _{STG}	-55~+175	°C

THERMAL CHARACTERISTICS Characteristic Condition Symbol Typical Unit Thermal resistance, junction - case R_{th(j-C)} 0.58 °C/W

ELECTRICAL CHARATERISTICS (at $T_c = 25$ °C, unless otherwise specified)

Characteristic	Symbol	Min.	Тур.	Max.	Unit
DC Blocking Voltage	V _{DC}	650			V
Forward Voltage IF = 10A IF = 20A, Tc =25°C IF = 20A, Tc =175°C	V _F		1.16 1.35 1.70	1.6	V
Reverse Current VR = 650V, Tc =25℃ VR = 650V, Tc =175℃	I _R		6 15	100	uA
Total Capacitive Charge VR = 400V	Q _C		62		nC
Total capacitance VR = 1V, f =1MHz VR = 200V, f =1MHz VR = 400V, f =1MHz	С		906 122 118		pF
Capacitance Stored Energy VR = 400 V	Ec		10		uJ

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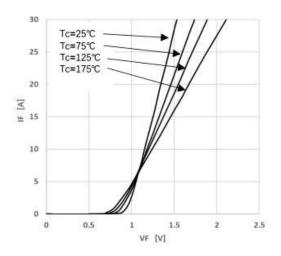


Figure 1. Forward characteristics

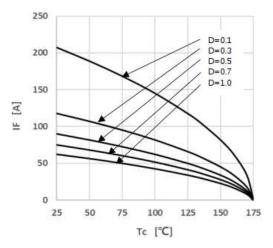


Figure 3. Peak Forward Current Derating

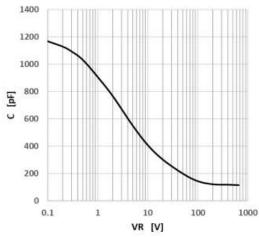


Figure 5. Capacitance vs. Reverse Voltage

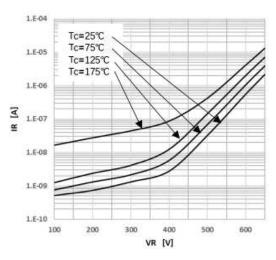


Figure 2. Reverse characteristics

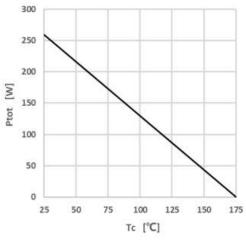


Figure 4. Power Dissipation

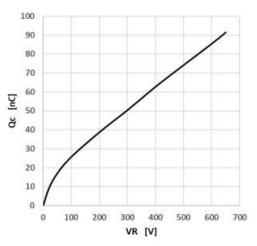


Figure 6. Capacitance Charge vs. Reverse Voltage

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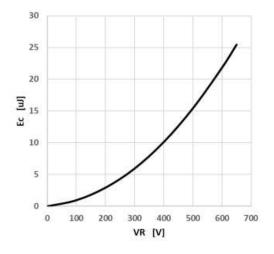


Figure 7. Capacitance Stored Energy

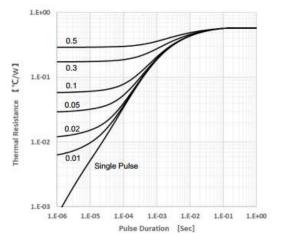
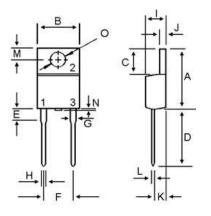


Figure 8. Transient Thermal Impedance

Circuit diagram



TO-220AC Package outlines : Dimensions in (mm)



DIM	MILLIMETERS		
DIN	MIN	MAX	
А	14.68	16.00	
В	9.78	10.42	
С	5.02	6.60	
D	13.00	14.62	
ш	3.10	4.19	
F	4.82	5.34	
G	1.10	1.67	
Н	0.69	1.01	
I	4.22	4.98	
J	1.14	1.40	
K	2.20	3.30	
L	0.28	0.61	
М	2.48	3.00	
Ν		2.00	
0	3.50	4.00	



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